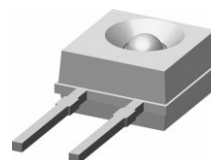


GaAs Infrared Emitting Diode in Side View Package

Description

TSKS5400S is a standard GaAs infrared emitting diode in a flat sideview, molded plastic package. A small recessed spherical lens provides an improved radiant intensity in a low profile package.

The device diode is package compatible to TEKT5400S, phototransistor and to TEKS5400 photodetector, allowing the user to assemble his own optical sensor.



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Features

- Side view package with spherical lens
- Radiation direction perpendicular to mounting direction
- Angle of half sensitivity $\phi = \pm 30^\circ$
- Peak wavelength $\lambda_P = 950 \text{ nm}$
- Package compatible to TEKT5400S

Order Instruction

| Ordering Code | Remarks |
|---------------|---|
| TSKS5400S | 2000 pcs in Plastic Bags |
| TSKS5400S-ASZ | 2.54 mm Pin distance (lead to lead), height of taping 16 mm |

Absolute Maximum Ratings

 $T_{amb} = 25^\circ\text{C}$

| Parameter | Test Conditions | Symbol | Value | Unit |
|--------------------------------------|---------------------------------------|------------|------------|------------------|
| Reverse voltage | | V_R | 6 | V |
| Forward current | | I_F | 100 | mA |
| Surge forward current | $t_p \leq 100 \mu\text{s}$ | I_{FSM} | 2 | A |
| Power dissipation | | P_V | 170 | mW |
| Junction temperature | | T_j | 100 | $^\circ\text{C}$ |
| Operating temperature range | | T_{stg} | -25...+85 | $^\circ\text{C}$ |
| Storage temperature range | | T_{stg} | -40...+100 | $^\circ\text{C}$ |
| Soldering temperature | $t \leq 5 \text{ s}$, 2 mm from body | T_{sd} | 260 | $^\circ\text{C}$ |
| Thermal resistance junction/ ambient | | R_{thJA} | 450 | k/W |

Basic Characteristics

$T_{amb} = 25^{\circ}\text{C}$

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Unit |
|-------------------------------|--|-----------------|------|----------|------|------------|
| Forward voltage | $I_F = 100\text{ mA}$, $t_p \leq 20\text{ ms}$ | V_F | | 1.3 | 1.7 | V |
| Reverse voltage | $I_R = 10\text{ }\mu\text{A}$ | V_{VR} | 6 | | | V |
| Junction capacitance | $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ | C_j | | 50 | | pF |
| Radiant intensity | $I_F = 50\text{ mA}$, $t_p \leq 20\text{ ms}$ | I_e | 2 | | 7 | mW/ sr |
| Radiant power | $I_F = 50\text{ mA}$, $t_p \leq 20\text{ ms}$ | ϕ_e | | 10 | | mW |
| Temp. coefficient of ϕ_e | $I_F = 50\text{ mA}$ | TK_{ϕ_e} | | -1.0 | | %K |
| Angle of half sensitivity | | ϕ | | ± 30 | | $^{\circ}$ |
| Peak wavelength | $I_F = 50\text{ mA}$ | λ_p | | 950 | | nm |
| Spectral bandwidth | $I_F = 50\text{ mA}$ | $\Delta\lambda$ | | 50 | | nm |
| Rise time | $I_F = 1\text{ A}$, $t_p/T = 0.01$, $t_p \leq 10\text{ }\mu\text{s}$ | t_r | | 400 | | ns |
| Fall time | $I_F = 1\text{ A}$, $t_p/T = 0.01$, $t_p \leq 10\text{ }\mu\text{s}$ | t_f | | 450 | | ns |

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

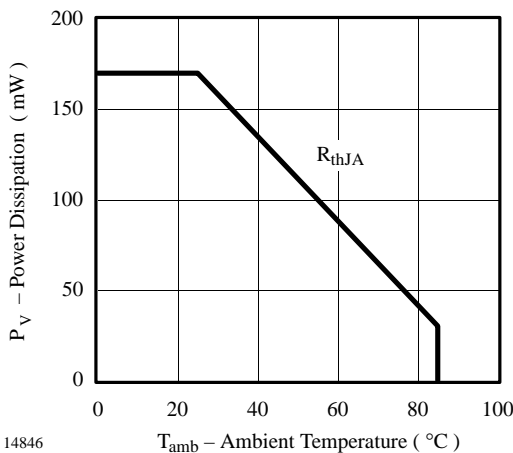


Figure 1. Power Dissipation vs. Ambient Temperature

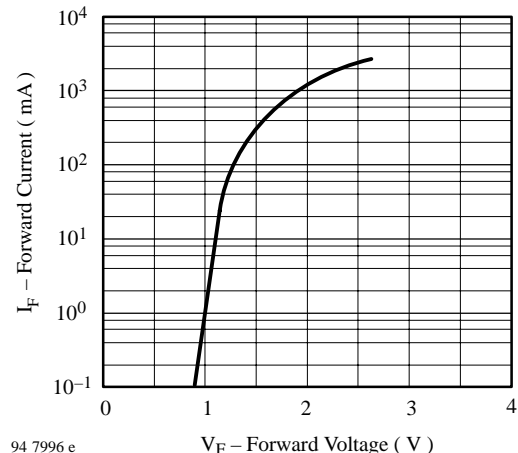


Figure 3. Forward Current vs. Forward Voltage

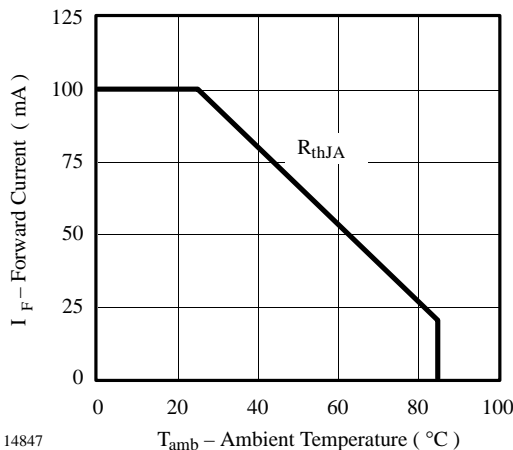


Figure 2. Forward Current vs. Ambient Temperature

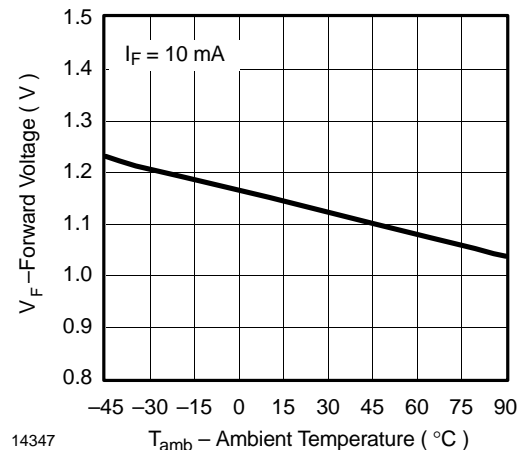


Figure 4. Forward Voltage vs. Ambient Temperature

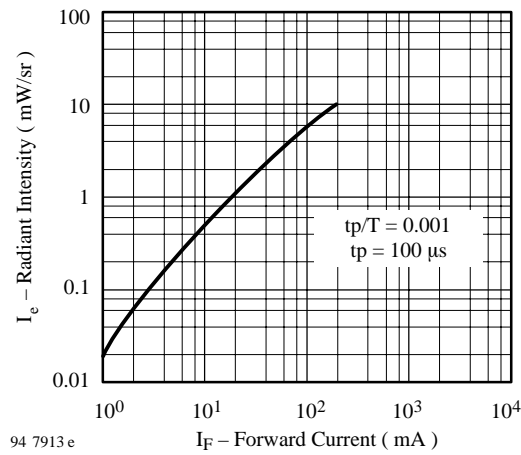


Figure 5. Radiant Intensity vs. Forward Current

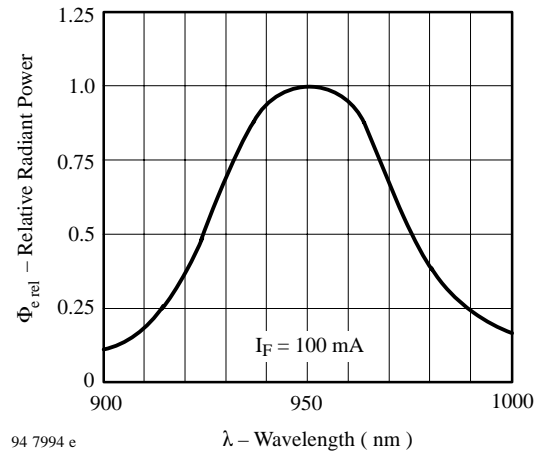


Figure 8. Relative Radiant Power vs. Wavelength

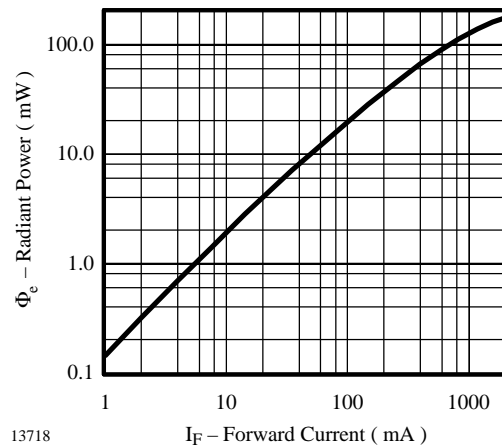


Figure 6. Radiant Power vs. Forward Current

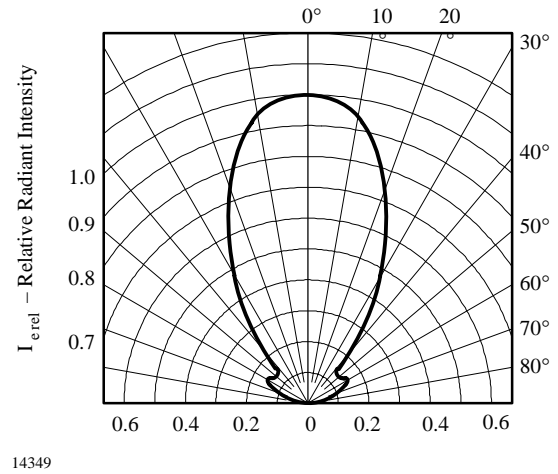


Figure 9. Relative Radiant Intensity vs. Angular Displacement

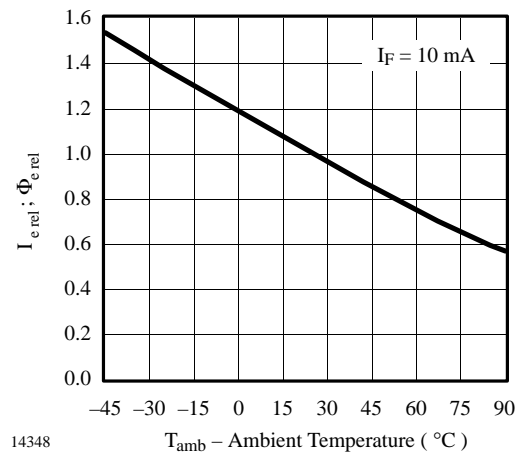
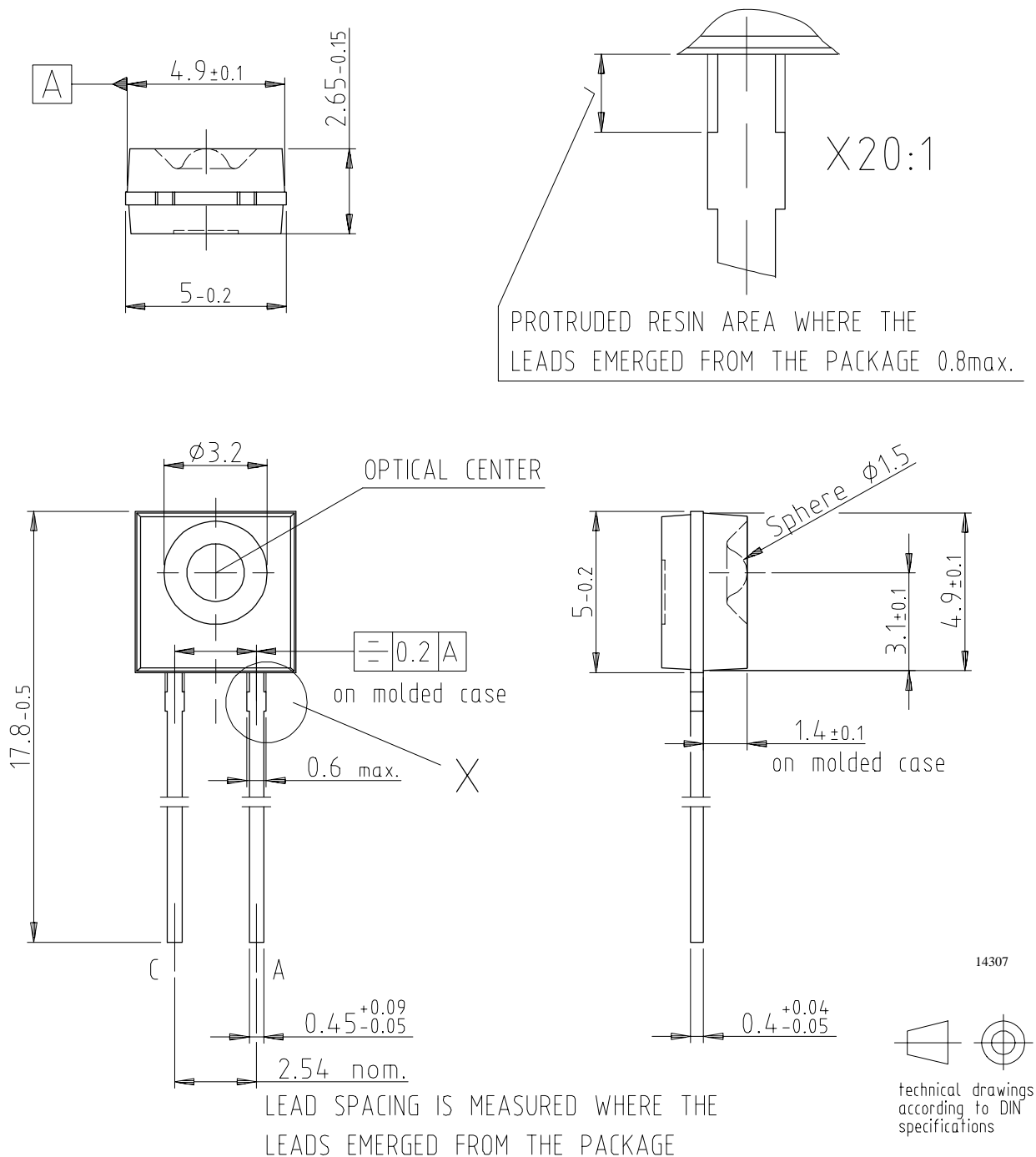


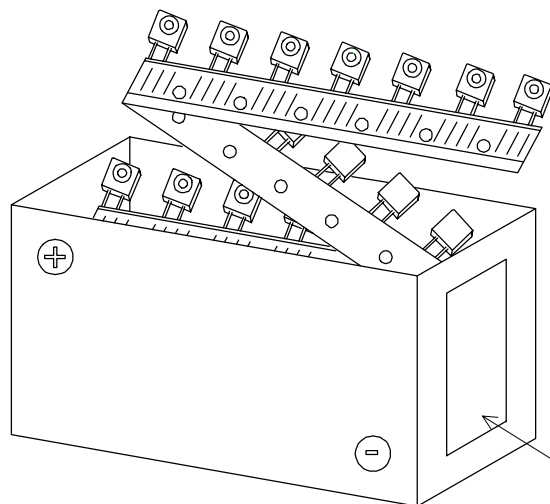
Figure 7. Relative Radiant Intensity vs. Ambient Temperature

Dimensions of TSKS5400S in mm

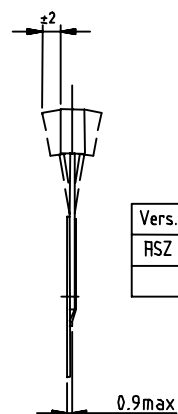
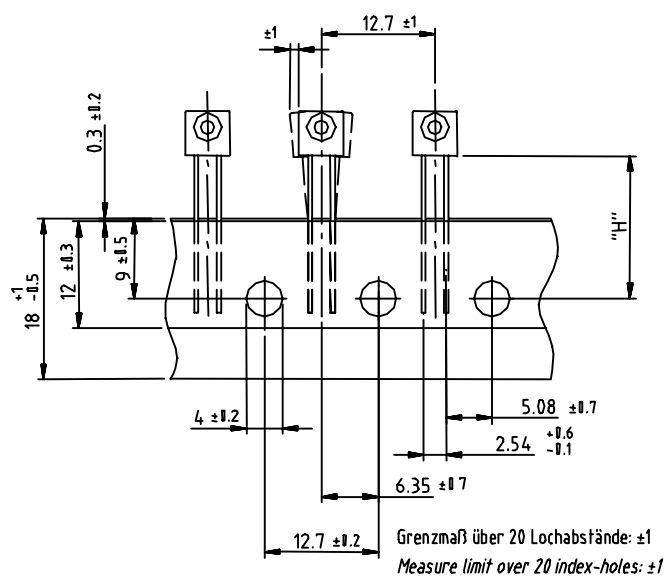




Tape and Ammopack Standards



Kennzeichnung: Barcode-Etikett siehe 5.6.4
Labeling: Barcode-label see 5.6.4



| Vers. | Dim. "H" |
|-------|----------|
| RSZ | 16 ±0.5 |

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Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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